

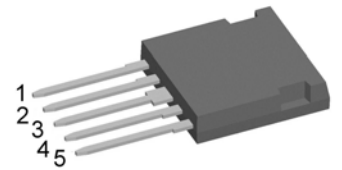
## Standard Rectifier

<b>3~ Rectifier</b>	
$V_{RRM}$	= 1600 V
$I_{DAV}$	= 50 A
$I_{FSM}$	= 270 A


### 3~ Rectifier Bridge

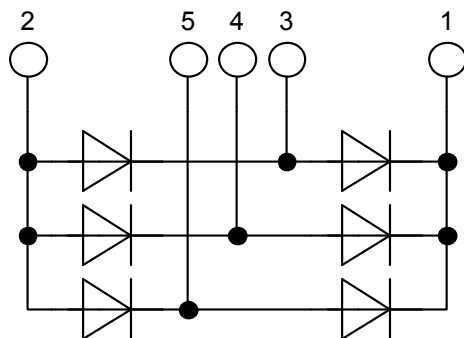
Part number

FUO50-16N



Backside: isolated

 E72873



#### Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

#### Applications:

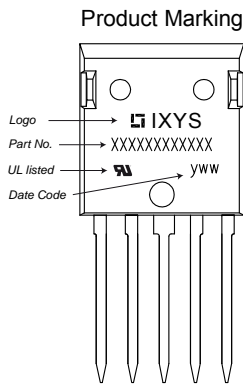
- Diode for main rectification
- For single and three phase bridge configurations

#### Package: i4-Pac

- Isolation Voltage: 3000V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1600	V
$I_R$	reverse current, drain current	$V_R = 1600 V$	$T_{VJ} = 25^{\circ}C$		20	$\mu A$
		$V_R = 1600 V$	$T_{VJ} = 150^{\circ}C$		1	mA
$V_F$	forward voltage drop	$I_F = 15 A$	$T_{VJ} = 25^{\circ}C$		1.15	V
		$I_F = 45 A$			1.50	V
		$I_F = 15 A$	$T_{VJ} = 150^{\circ}C$		1.04	V
		$I_F = 45 A$			1.55	V
$I_{DAV}$	bridge output current	$T_C = 120^{\circ}C$ rectangular $d = 1/3$	$T_{VJ} = 175^{\circ}C$		50	A
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0.78	V
$r_F$	slope resistance				17	m $\Omega$
$R_{thJC}$	thermal resistance junction to case				2.1	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.20		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		70	W
$I_{FSM}$	max. forward surge current	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		270	A
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		290	A
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		230	A
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		250	A
$I^2t$	value for fusing	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		365	A <sup>2</sup> s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		350	A <sup>2</sup> s
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		265	A <sup>2</sup> s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		260	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400 V; f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		8	pF

Package i4-Pac		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			50	A
$T_{stg}$	storage temperature		-55		150	°C
$T_{VJ}$	virtual junction temperature		-55		175	°C
<b>Weight</b>				9		g
$F_C$	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	1.7			mm
$d_{Spb/Apb}$		terminal to backside	5.1			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	FUO50-16N	FUO50-16N	Tube	25	498637

### Equivalent Circuits for Simulation

\* on die level

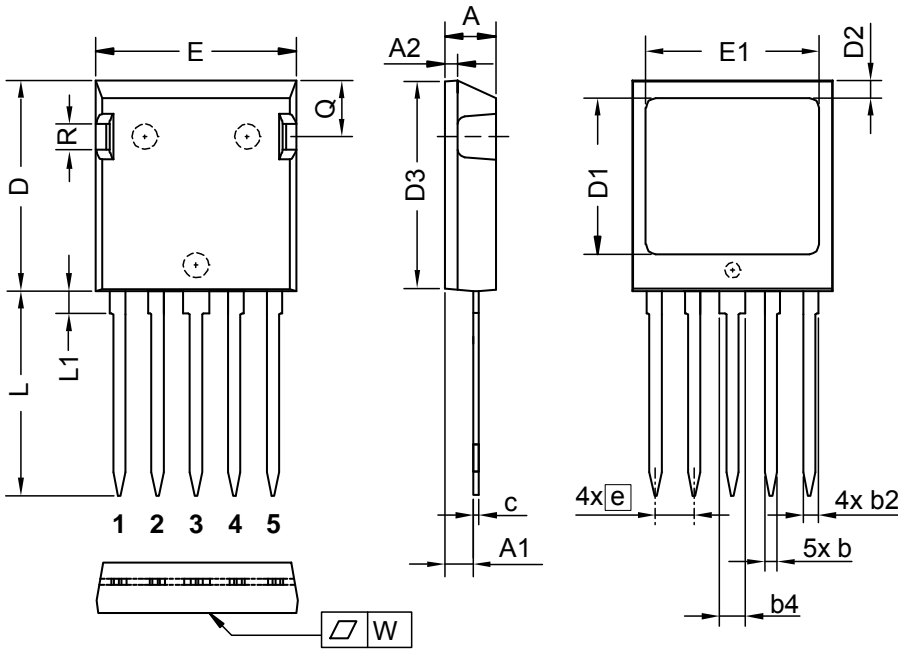
$T_{VJ} = 175^{\circ}C$



Rectifier

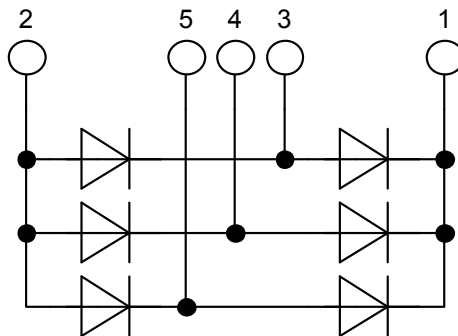
$V_{0\ max}$	threshold voltage	0.78	V
$R_{0\ max}$	slope resistance *	14	mΩ

## Outlines i4-Pac



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81 BSC		0.150 BSC	
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite  
 The convexbow of substrate is typ. < 0.05 mm over plastic surface level of device bottom side



**Rectifier**

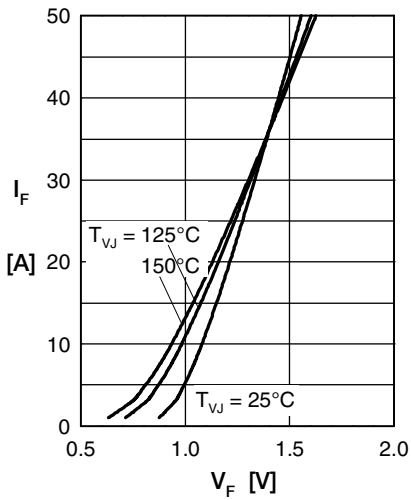


Fig. 1 Forward current versus voltage drop per diode

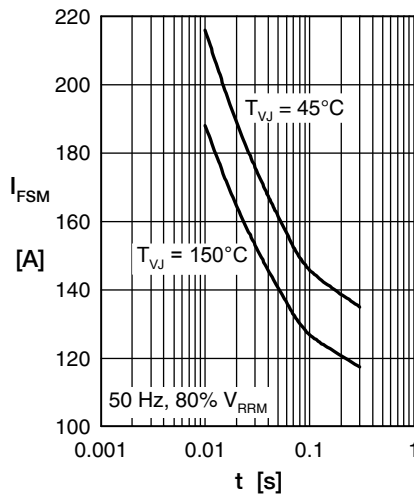


Fig. 2 Surge overload current

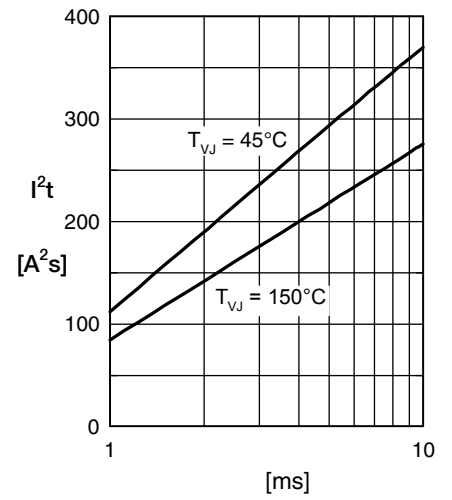


Fig. 3  $I^2t$  versus time per diode

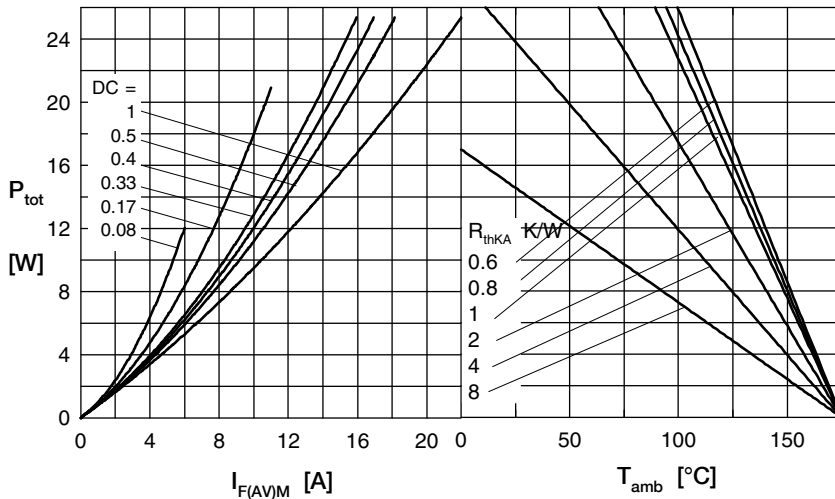


Fig. 4 Power dissipation vs. direct output current & ambient temperature

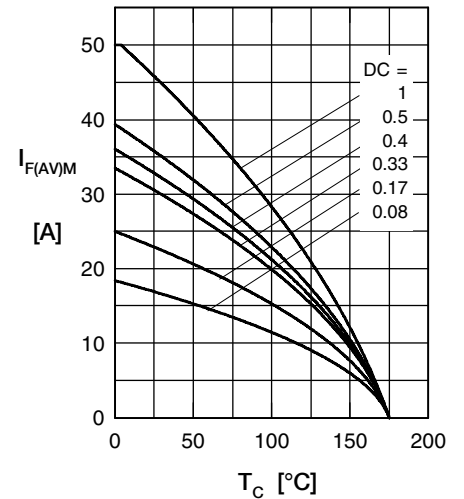


Fig. 5 Max. forward current vs. case temperature

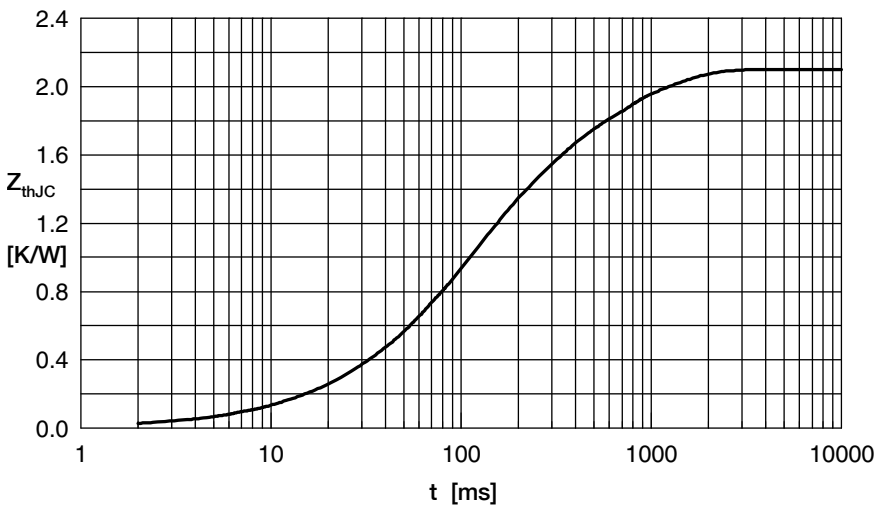


Fig. 6 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	1.159	0.1015
2	0.1286	0.1026
3	0.2651	0.4919
4	0.5473	0.62